

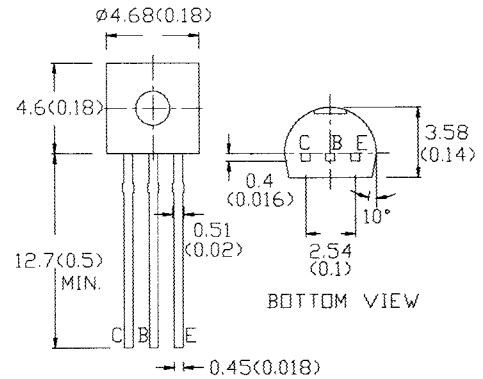
MICRO ELECTRONICS

**NPN
SILICON
TRANSISTOR**

DESCRIPTION

CL5822 is silicon planar transistors for use in AF drivers and outputs, as well as for universal applications.

TO-92A



UNIT: MM(INCH)

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage ($I_B=0$)	V_{CEO}	60V
Collector-Emitter Voltage ($V_{EB}=0$)	V_{CES}	70V
Emitter-Base Voltage	V_{EBO}	5V
Collector Current	I_C	1A
Continuous Power Dissipation	P_d	625mW
Operating & Storage Junction Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	V_{CEO}^*	60		V	$I_C=10\text{mA}$ $I_B=0$
Collector-Emitter Breakdown Voltage	V_{CES}	70		V	$I_C=0.01\text{mA}$ $V_{EB}=0$
Collector Cutoff Current	I_{CBO}		100	nA	$V_{CB}=25\text{V}$ $I_E=0$
Emitter Cutoff Current	I_{EBO}		10	μA	$V_{EB}=5\text{V}$ $I_C=0$
D.C. Current Gain	H_{FE}^*	100	200		$I_C=2\text{mA}$ $V_{CE}=2\text{V}$
		25			$I_C=500\text{mA}$ $V_{CE}=2\text{V}$
Base-Emitter Voltage	V_{BE}^*		1.1	V	$I_C=500\text{mA}$ $V_{CE}=2\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$		0.75	V	$I_C=500\text{mA}$ $I_B=50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}^*$		1.2	V	$I_C=500\text{mA}$ $I_B=50\text{mA}$
Output Capacitance	C_{ob}		15	pF	$V_{CB}=10\text{V}$ $I_E=0$ $f=1\text{MHz}$
Current Gain-Bandwidth Product	f_T	140	TYP	MHz	$I_C=50\text{mA}$ $V_{CE}=2\text{V}$

* Pulse test : pulse width $<300\mu\text{S}$, duty cycle $<2\%$.



MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

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